

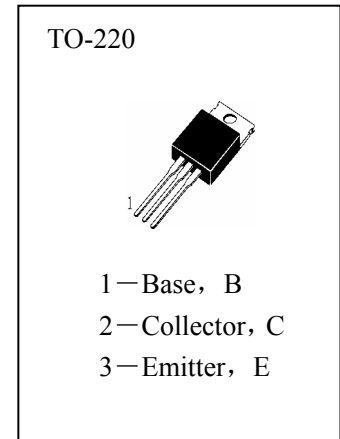


APPLICATIONS

PNP Epitaxial Darlington Transistor. High DC Current Gain. Monolithic Construction with Built-In Base-Emitter Shunt Resistors.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

- Tstg—Storage Temperature... -55~150°C
Tj—Junction Temperature... 150°C
Pc—Collector Dissipation(Tc=25°C)... 65W
Pc—Collector Dissipation (Ta=25°C) ... 2W
Vcbo—Collector-Base Voltage... -100V
Vceo—Collector-Emitter Voltage... -100V
Veb0—Emitter-Base Voltage... -5V
Ic—Collector Current (DC) ... -5A
Ic—Collector Current (Pulse) ... -8A
Ib—Base Current... -120mA



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Table with 7 columns: Symbol, Characteristics, Min, Typ, Max, Unit, Test Conditions. Rows include BVcbo, BVceo, HFE, VCE(sat1), VCE(sat2), VBE(ON), ICEO, ICBO, IEBO, and Cob.

\*Pulse Test: PW ≤ 300 μs, Duty cycle ≤ 2%

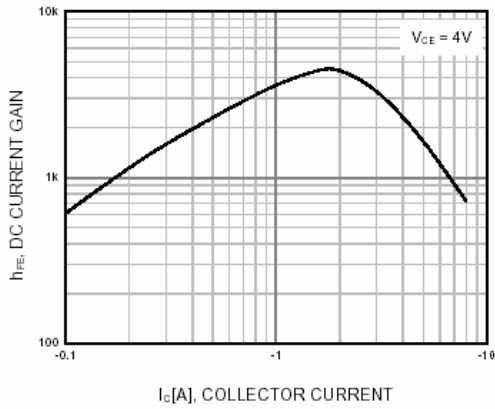


Figure 1. DC current Gain

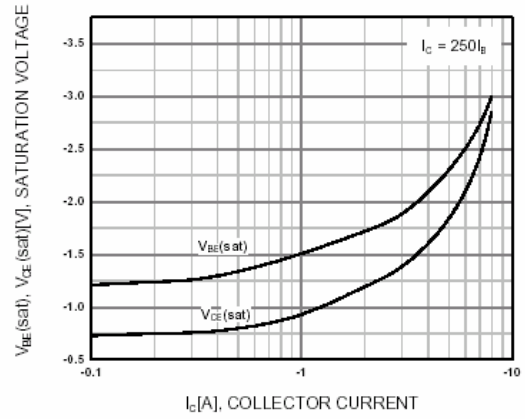


Figure 2. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

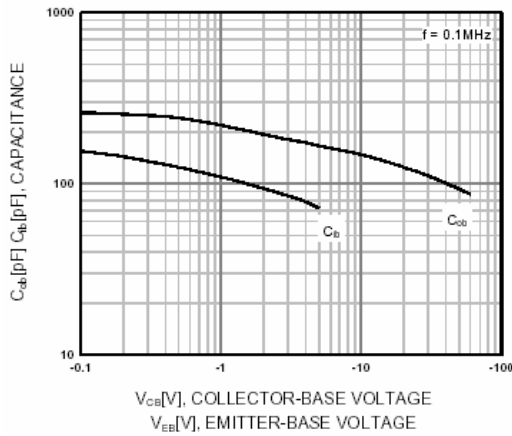


Figure 3. Output and Input Capacitance  
vs. Reverse Voltage

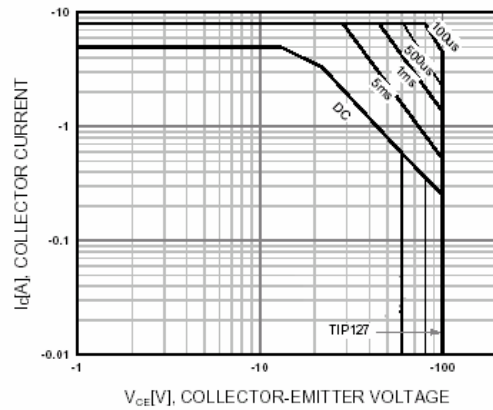


Figure 4. Safe Operating Area

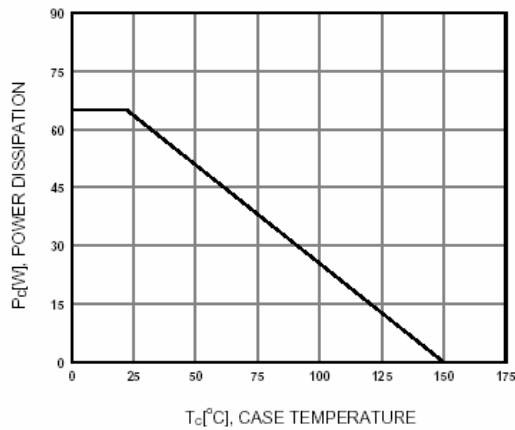


Figure 5. Power Derating